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Microsemi

Power Matters[™]

100.00

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2N4914 (#23234)

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Overview Diagrams

Electrical Rating Symbol Min Typ Max Collector to Emitter Saturation Voltage V_{CE(Sat)} 0.75

HFE

Maximum Electrical Rating	Symbol	Min	Тур	Max	Unit
Breakdown Voltage, Collector-Base (Emitter Open)	V _{BR(CBO)}			60.00	V
Collector Current (dc)	I _C			5.00	А
Collector-Emitter Voltage (Base Open)	V _{CEO}			60.00	V
Emitter-Base Voltage (Collector Open)	V _{EBO}			5.00	V
Power Dissipation, Total	P _T			88.00	W

This part can be found in the following product categories:

- → Discretes → Transistors → BJT(BiPolar Junction Transistor) → PNP Transistor
- Non-Radiation Hardened Devices Transistors BJT(BiPolar Junction Transistor) NPN Transistor

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